

### **IN THE CLAIMS**

This listing of the claims replaces all prior listings.

#### **Listing of Claims:**

1. (Currently Amended) A semiconductor device comprising:
  - a substrate;
  - a first insulation film formed on the substrate;
  - a first conductive layer formed on the substrate with the first insulation film positioned between the substrate and the first conductive layer;
  - a second conductive layer formed on the substrate at a predetermined distance from the first conductive layer;
  - a second insulation film formed on upper surfaces of the first conductive layer and the second conductive layer and having a plurality of first opening portions to expose either the first conductive layer or the second conductive layer and one or more second opening portions to expose neither the first conductive layer nor the second conductive layer and expose the first insulation film; and
  - a third conductive layer formed on an upper surface of the second insulation film in such a manner to fill up the first opening portions and the second opening portions for making electrical connection between the first conductive layer and the second conductive layer by way of the first opening portions;wherein,
  - the second opening portions are formed between a pair of the first opening portions along the third conductive layer, and
  - the second insulation film is formed by a low dielectric constant material having a lower Young's modulus than that of a SiO<sub>2</sub> film or a SiO<sub>2</sub> film containing fluorine.
2. (Original) The semiconductor device of claim 1, wherein the second opening portions are formed at a predetermined distance between the first opening portions.

3. (Original) The semiconductor device of claim 1, wherein the third conductive layer is formed by a conductive material containing copper.

4. (Currently Amended) A semiconductor device comprising:  
a substrate;  
a first insulation film formed on the substrate;  
a first conductive layer formed on the substrate with the first insulation film positioned between the substrate and the first conductive layer;  
a second conductive layer formed on the substrate at a predetermined distance from the first conductive layer;  
a second insulation film formed on upper surfaces of the first conductive layer and the second conductive layer and having a plurality of opening portions to expose one end portion of the first conductive layer or of the second conductive layer or the first insulation film; and  
a third conductive layer formed on an upper surface of the second insulation film in such a manner to fill up the opening portions for making electrical connection between the first conductive layer and the second conductive layer;  
wherein,  
the third conductive layer has a predetermined wiring length to maintain the connection even if the length of the third conductive layer in a direction of longer length changes due to thermal expansion or contraction, and has the electrical connection between the first conductive layer and the second conductive layer at both ends of the third conductive layer by way of the opening portions, and  
the second insulation film is formed by a low dielectric constant material having a lower Young's modulus than that of a SiO<sub>2</sub> film or a SiO<sub>2</sub> film containing fluorine.

5. (Original) The semiconductor device of claim 4, wherein the third conductive layer is formed by a conductive material containing copper.

6. (Withdrawn) The method of fabricating a semiconductor device, comprising the steps of:

forming a first conductive layer on a substrate;

forming a second conductive layer on the substrate at a predetermined distance from the first conductive layer;

forming an insulation film on upper surfaces of the first conductive layer and the second conductive layer;

forming in the insulation film a plurality of first opening portions to expose either the first conductive layer or the second conductive layer and a plurality of second opening portions to expose neither the first conductive layer nor the second conductive layer; and

forming a third conductive layer on an upper surface of the insulation film in such a manner to fill up the first opening portions and the second opening portions for making electrical connection between the first conductive layer and the second conductive layer by way of the opening portions;

wherein

the second opening portions are formed between a pair of the first opening portions along the third conductive layer.

7. (Withdrawn) A method of fabricating a semiconductor device, comprising the steps of:

forming a first conductive layer on a substrate;

forming a second conductive layer on the substrate at a predetermined distance from the first conductive layers;

forming an insulation film on upper surfaces of the first conductive layers and the second conductive layers;

forming in the insulation film a plurality of opening portions to expose either one end portion of the first conductive layer or of the second conductive layer; and

forming a third conductive layer on an upper surface of the insulation film in such a manner to fill up the opening portions and to make electrical connection with the first conductive layer and the second conductive layer;

wherein

the third conductive layer has a predetermined wiring length to maintain the connection even if the length of the third conductive layers in a direction of longer length changes due to thermal expansion or contraction, and has the electrical connection between the first conductive layer and the second conductive layer at both ends of the third conductive layer by way of the opening portions.